



STF16NM50N Information



For Reference Only

Part Number STF16NM50N

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 15A TO-220FP

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









STF16NM50N Specifications

Manufacturer Part Number STF16NM50N Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 15A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 260 mOhm @ 7.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Torain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 15A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1200pF @ 50V Vgs (Max) Vgs (Max) **ET Feature **Dower Dissipation (Max) Rds On (Max) **Go m Ohm @ 7.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Supplier Device Package Package / Case TO-220FP Package / Case	Manufacturer Part Number	STF16NM50N
Package TO-220-3 Full Pack Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 15A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 260 mOhm @ 7.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Manufacturer	STMicroelectronics
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Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 15A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 260 mOhm @ 7.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C15A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs260 mOhm @ 7.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Package	TO-220-3 Full Pack
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C15A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs260 mOhm @ 7.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Series	MDmesh? II
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C15A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs260 mOhm @ 7.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case 150 (Tc) 15A (Tc) 15A (Tc) 15A (Tc) 15A (Tc) 15A (Tc) 15A (Tc) 15V 15V 250µA 38nC @ 10V 1200pF @ 50V 25V 25V 260 mOhm @ 7.5A, 10V 150°C (TJ) Through Hole	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs260 mOhm @ 7.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Supplier Device Package Package / Case 4V @ 250μA 38nC @ 10V 1200pF @ 50V ±25V FET Feature - 260 mOhm @ 7.5A, 10V Through Hole Through Hole	Current - Continuous Drain (Id) @ 25°C	15A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 50V Vgs (Max) ±25V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 260 mOhm @ 7.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) EET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case 1200pF @ 50V 100pF @	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs260 mOhm @ 7.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	38nC @ 10V
FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 260 mOhm @ 7.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	1200pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 260 mOhm @ 7.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs260 mOhm @ 7.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	30W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	260 mOhm @ 7.5A, 10V
Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Operating Temperature	150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220FP
Report errors?	Package / Case	TO-220-3 Full Pack
•		Report errors?

STF16NM50N Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STF16NM50N Payment Methods



















STF16NM50N Shipping Methods













If you have any question about STF16NM50N, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com